Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (amended): A method for rf power amplifying which comprises:

a) series connecting upper and lower solid-state current devices;

b) said series connecting step comprises connecting a lower-voltage terminal of said upper solid-state current device to an rf choke, and connecting said rf choke to a higher-voltage terminal of said lower solid-state current device;

c) separately amplifying rf signals in said solid-state current devices at a selected operating frequency;

d) rf decoupling said solid-state current devices;

e) said rf decoupling step comprises providing a capacitance between said lower-voltage terminal and an electrical ground; and

f) said rf decoupling step further comprises making an rf effective series resistance of said capacitance lower than that of any porcelain capacitor that resonates at said selected operating frequency.

2 (new). A method as claimed in Claim 1 in which said step of making an rf effective series resistance lower than that of any porcelain capacitor comprises making two capacitors function as parallel-connected capacitors.

3 (new). A method as claimed in Claim 1 in which said method further comprises:

a) splitting an rf input into said rf signals prior to said separate amplifying step; and

b) combining said separately amplified rf signals.

4 (new). A method as claimed in Claim 2 in which said rf decoupling step further comprises selecting two of said capacitors to resonate at substantially the same frequency.

5 (new). A method as claimed in Claim 2 in which said rf decoupling step further comprises:

a) selecting one of said capacitors to resonate at a frequency that is higher than said selected operating frequency; and

b) selecting another of said capacitors to resonate at a frequency that is lower than said selected operating frequency.

6 (new). A method as claimed in Claim 2 in which said rf decoupling step further comprises:

a) selecting two of said capacitors to resonate at frequencies that are higher than said selected operating frequency; and

b) selecting an other two of said capacitors to resonate at frequencies that are lower than said selected operating frequency.

7 (new). A method as claimed in Claim 2 in which said rf decoupling step further comprises:

a) selecting two of said capacitors to resonate at separate frequencies that are both higher than said selected operating frequency; and

b) selecting an other two of said capacitors to resonate at separate frequencies that are both lower than said selected operating frequency.

8 (new). A method as claimed in Claim 2 in which:

a) said method further comprises disposing said selected operating frequency within a broad band of operating frequencies;

b) said rf decoupling step further comprises selecting a first plurality of said capacitors to resonate in a higher-frequency portion of said broad band; and

c) said rf decoupling step still further comprises selecting a second plurality of said capacitors to resonate in a lower-frequency portion of said broad band.

9 (new). A method as claimed in Claim 1 in which:

a) said method further comprises disposing said selected operating frequency within a broad band of operating frequencies;

b) said rf decoupling step further comprises making an rf effective series resistance of said capacitance lower than that of any porcelain capacitor that resonates in a higher-frequency of said broad band; and

c) said rf decoupling step still further comprises making an rf effective series resistance of another capacitance lower than that of any porcelain capacitor that resonates in a lower-frequency of said broad band.

10 (new). A method as claimed in Claim 1 in which:

a) said method for rf power amplifying further comprises series connecting a third solid-state current device with said upper and lower solid-state current devices;

b) said method further comprises supplying a variable voltage to a control terminal of said third solid-state current device; and

c) said method still further comprises controlling an rf output of one of said amplified rf signals as a function of said variable voltage.

11 (new). A method as claimed in Claim 1 in which:

a) said separate amplifying step comprises rf amplifying one of said rf signals at varying frequencies; and

b) said method comprises flattening an rf output of one of said amplified rf signals with respect to said varying frequencies.

12 (new). A method as claimed in Claim 1 in which:

a) said method comprises series connecting a third solid-state current device with said upper and lower solid-state current devices;

b) said separate amplifying step comprises amplifying said rf signals at equal and varying frequencies;

c) said method further comprises combining said separately amplified rf signals into a single rf output;

d) said method still further comprises flattening said single rf output with respect to said varying frequencies; and

e) said flattening step comprises detecting said single rf output, using said detected rf output to control said third solid-state current device, and using said third solid-state current device to control said separate amplifying steps.

13 (new). A method as claimed in Claim 1 in which:

a) said method comprises series connecting a third solid-state current device with said upper and lower solid-state current devices;

b) increasing current flow through two of said solid-state current devices with respect to said current flow through another of said solid-state current devices; and

c) said increasing step comprises shunting current flow around said other solid-state current device.

14 (new). A method as claimed in Claim 1 in which said method comprises:

a) series connecting a third solid-state current device with said upper and lower solid-state current devices;

b) amplifying an rf input in said third solid-state current device; and

c) splitting said amplified rf input into said rf signals.

15 (new). A method as claimed in Claim 1 in which said method comprises:

a) series connecting third and fourth solid-state current devices with said upper and lower solid-state current devices;

b) amplifying an rf input in said third solid-state current device;

c) splitting said amplified rf input into said rf signals;

d) supplying a variable voltage to a control terminal of said third solid-state current device; and

e) controlling power amplification of said upper and lower solid-state current devices as a function of said variable voltage.

16 (new). A method as claimed in Claim 1 in which said method comprises:

a) connecting third and fourth solid-state current devices in parallel; and

b) connecting said parallel-connected third and fourth solid-state current devices in series with said upper and lower solid-state current devices.

17 (new). A method as claimed in Claim 1 in which said method comprises:

a) connecting third and fourth solid-state current devices in parallel;

b) connecting said parallel-connected third and fourth solid-state current devices in series with said upper and lower solid-state current devices;

c) amplifying an rf input in said third solid-state current device;

d) splitting said amplified rf input into said rf signals;

e) delivering a variable control voltage to said fourth solid-state current device; and

f) controlling said separate amplifying steps as a function of said variable control voltage.

18 (new). A method as claimed in Claim 1 in which:

a) said method comprises splitting an rf input into said rf signals; and

b) said separate amplifying steps comprise producing separate rf outputs.

19 (new). A method as claimed in Claim 1 in which:

a) said method comprises splitting an rf input into said rf signals;

b) said separate amplifying steps comprise producing separate rf outputs; and

c) said method further comprises separately phase-shifting one of said separate rf outputs.

20 (new). A method as claimed in Claim 1 in which said method further comprises:

a) splitting an rf input into said rf signals and a third rf signal; and

b) separately amplifying said third rf signal.

21 (new). A method as claimed in Claim 1 in which said method further comprises:

a) splitting an rf input into said rf signals and a third rf signal;

b) separately amplifying said third rf signal; and

c) combining all of said separately amplified rf signals.

22 (new). A method as claimed in Claim 1 in which:

a) said method comprises series connecting a third solid-state current device with said upper and lower solid-state current devices;

b) supplying a variable-voltage input to said third solid-state current device;

c) producing a variable-frequency rf signal in said third solid-state current device that is a function of said variable-voltage input; and

d) splitting said variable-frequency rf signal into said rf signals.

23 (new). A method as claimed in Claim 1 in which said method comprises paralleling a third solid-state current device with one of said series-connected solid-state current devices.

24 (new). A method as claimed in Claim 1 in which:

a) said method further comprises rf decoupling a lower-voltage terminal of said lower solid-state current device; and

b) said rf decoupling step comprises making an effective series resistance between said lower-voltage terminal and said electrical ground lower than that of any porcelain capacitor that resonates at said selected operating frequency.

25 (new). A method as claimed in Claim 1 in which:

a) said method further comprises rf decoupling a lower-voltage terminal of said lower solid-state current device;

b) said rf decoupling step comprises making an effective series resistance between said lower-voltage terminal and said electrical ground lower than that of any porcelain capacitor that resonates at said selected operating frequency; and

c) said step of making an rf effective series resistance lower than that of any porcelain capacitor comprises making two capacitors function as parallel-connected capacitors.